

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

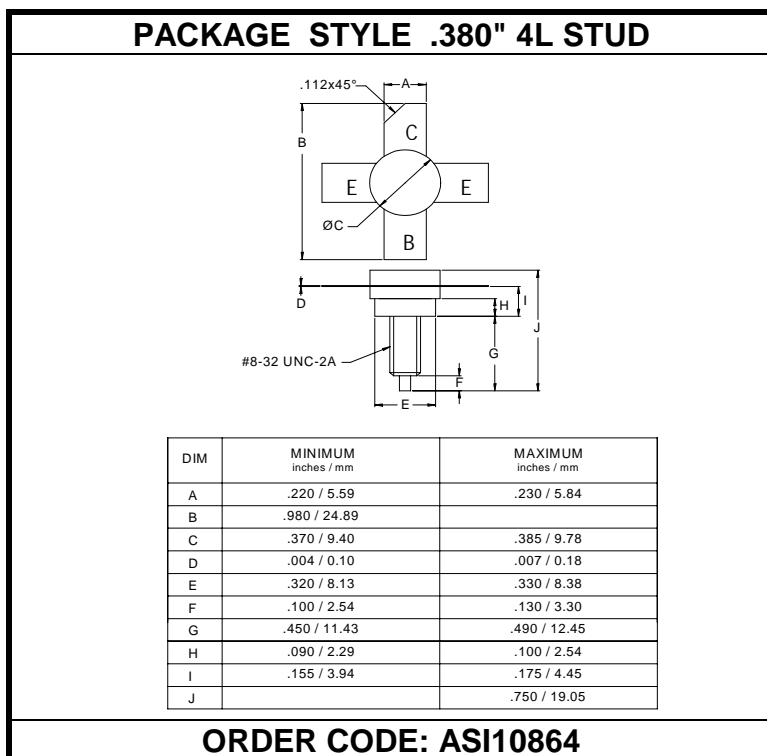
The **ASI 2N6199** is Designed for VHF Class C Power Amplifier Applications up to 250 MHz.

FEATURES:

- $P_G = 10$ dB Typical at 25 W/175 MHz
- ∞ Load VSWR at Rated Conditions
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB}	65 V
P_{DISS}	40 W @ $T_C = 25^\circ\text{C}$
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	4.4 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 200$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	10			---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz			50	pF
P_G	$V_{CE} = 28$ V $P_{OUT} = 25$ W $f = 175$ MHz	8.5	10		dB
η_c		50	60		%

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.